



PSMN5R6-100PS

N-channel 100 V 5.6 mΩ standard level MOSFET in TO220

Rev. 4 — 8 February 2012

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

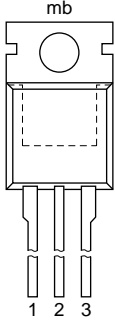
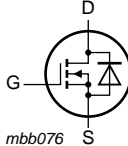
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	100	V
I_D	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see Figure 1	[1]	-	100	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ see Figure 2	-	-	306	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ see Figure 11 ; see Figure 12	-	4.3	5.6	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 80\text{ A}; V_{DS} = 50\text{ V};$ see Figure 13 ; see Figure 14	-	43	-	nC
$Q_{G(tot)}$	total gate charge		-	141	-	nC
Avalanche Ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C}; I_D = 100\text{ A}; V_{sup} \leq 100\text{ V}; R_{GS} = 50\text{ }\Omega;$ unclamped	-	-	468	mJ

[1] Continuous current limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN5R6-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

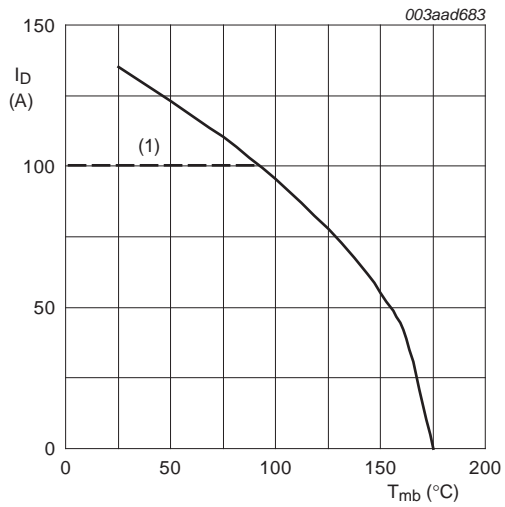
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

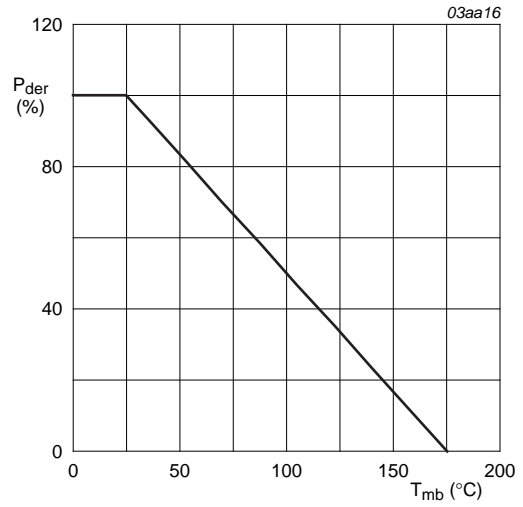
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	100	V
V_{DGR}	drain-gate voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_j = 100\text{ °C}$; see Figure 1	-	95	A
		$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$; see Figure 1	[1]	100	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; see Figure 3	-	539	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	306	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	[1]	100	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$	-	539	A
Avalanche Ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C}; I_D = 100\text{ A}; V_{sup} \leq 100\text{ V}; R_{GS} = 50\text{ }\Omega$; unclamped	-	468	mJ

[1] Continuous current limited by package.



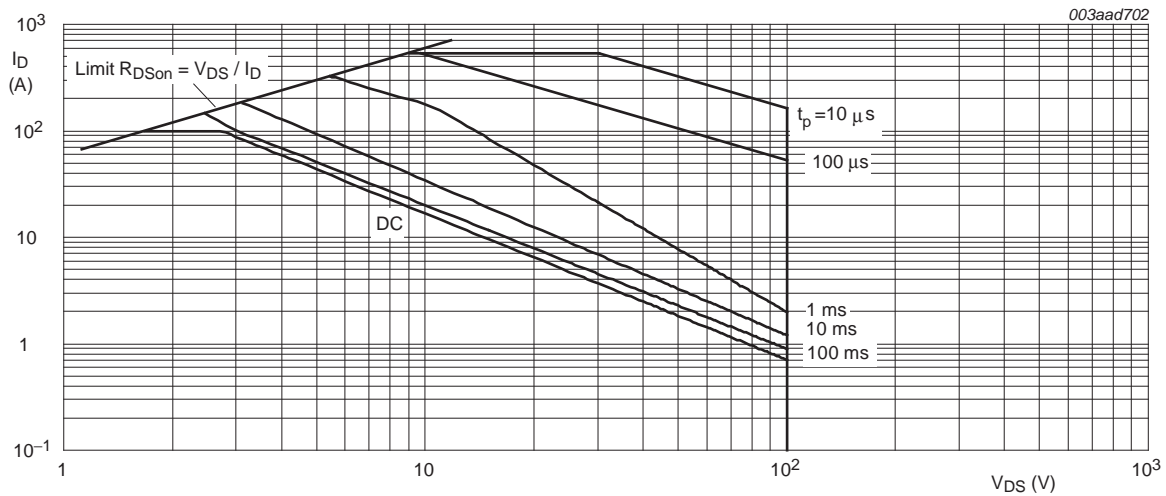
$V_{GS} \geq 10 \text{ V}$; (1) capped at 100 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25 \text{ }^\circ\text{C}$; Capped at 100 A due to package.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.3	0.49	K/W

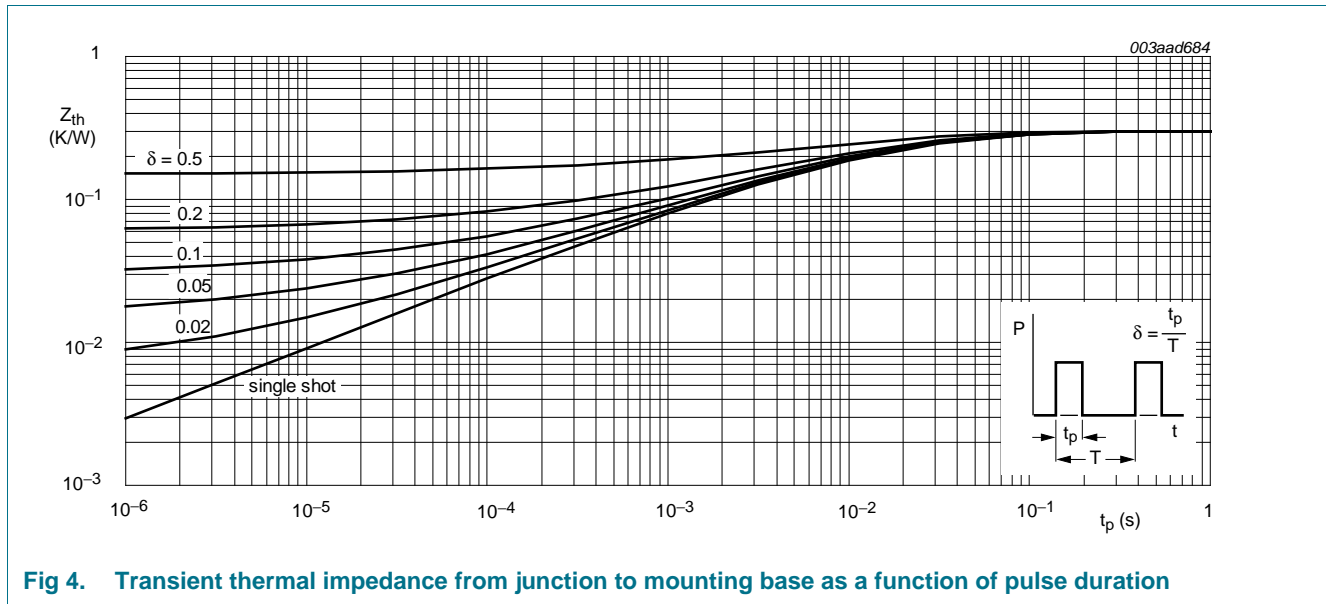
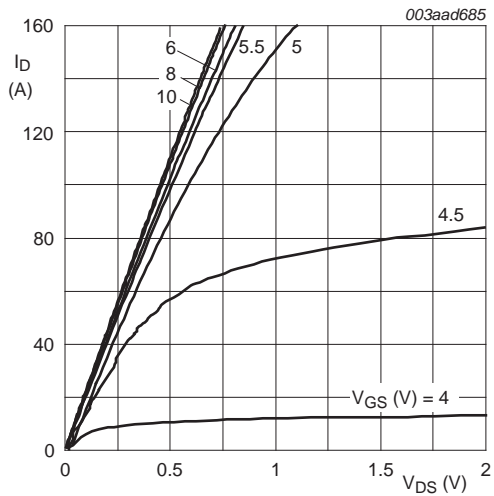


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

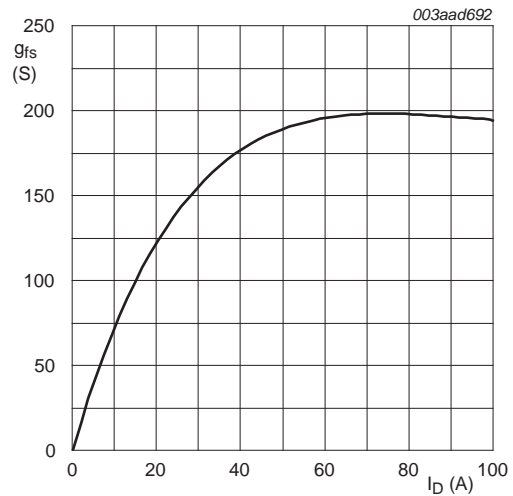
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	100	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$; see Figure 8 ; see Figure 9	2	3	4	V
V_{GSth}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C$; see Figure 9	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$; see Figure 9	-	-	4.6	V
I_{DSS}	drain leakage current	$V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.02	1	μA
		$V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 25 A; T_j = 175 \text{ }^\circ C$; see Figure 10	-	-	15.7	mΩ
		$V_{GS} = 10 V; I_D = 25 A; T_j = 25 \text{ }^\circ C$; see Figure 11 ; see Figure 12	-	4.3	5.6	mΩ
R_G	gate resistance	$f = 1 \text{ MHz}$	-	0.97	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 80 A; V_{DS} = 50 V; V_{GS} = 10 V$; see Figure 13 ; see Figure 14	-	141	-	nC
Q_{GS}	gate-source charge		-	36	-	nC
Q_{GD}	gate-drain charge		-	43	-	nC
C_{iss}	input capacitance	$V_{DS} = 50 V; V_{GS} = 0 V; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$; see Figure 15 ; see Figure 16	-	8061	-	pF
C_{oss}	output capacitance	$V_{DS} = 50 V; V_{GS} = 0 V; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$; see Figure 15	-	561	-	pF
C_{rss}	reverse transfer capacitance	$V_{DS} = 50 V; V_{GS} = 0 V; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$; see Figure 15 ; see Figure 16	-	330	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 50 V; R_L = 0.6 \text{ } \Omega; V_{GS} = 10 V$; $R_{G(ext)} = 1.5 \text{ } \Omega$	-	31	-	ns
t_r	rise time		-	46	-	ns
$t_{d(off)}$	turn-off delay time		-	83	-	ns
t_f	fall time		-	34	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$; see Figure 17	-	0.79	1.2	V
t_{rr}	reverse recovery time	$I_S = 25 A; di/dt = -100 A/\mu s; V_{GS} = 0 V$; $V_{DS} = 50 V$	-	67	-	ns
Q_r	recovered charge		-	182	-	nC



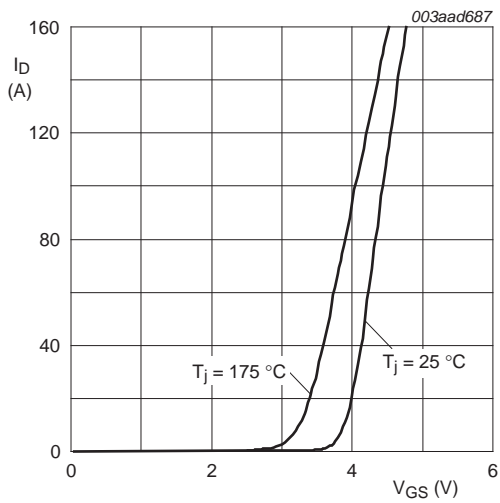
$T_j = 25\text{ }^\circ\text{C}; t_p = 300\text{ }\mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



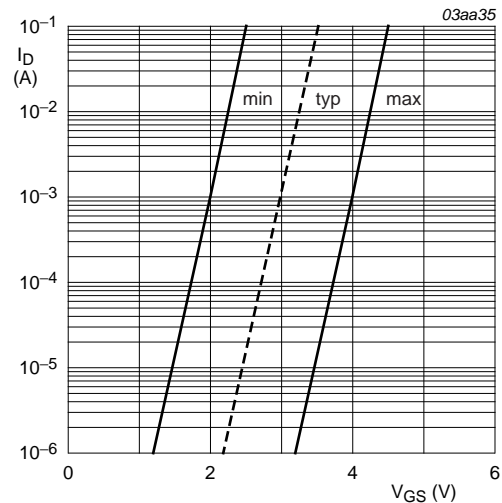
$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 25\text{ V}$

Fig 6. Forward transconductance as a function of drain current; typical values



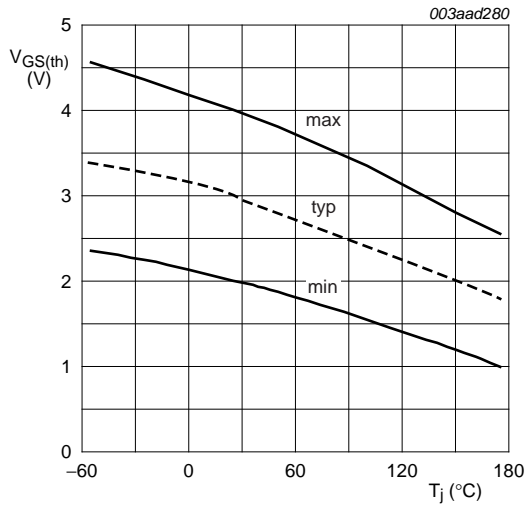
$V_{DS} = 25\text{ V}$

Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



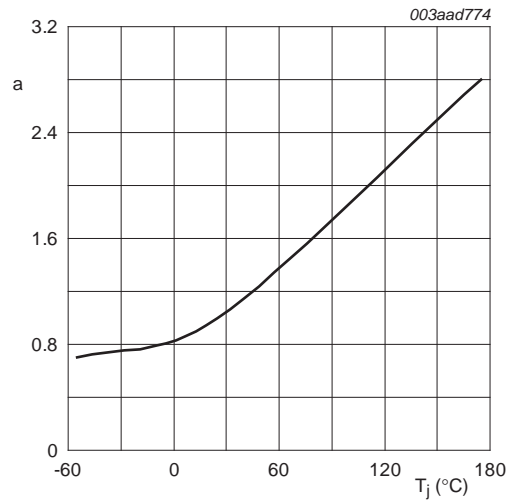
$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

Fig 8. Sub-threshold drain current as a function of gate-source voltage



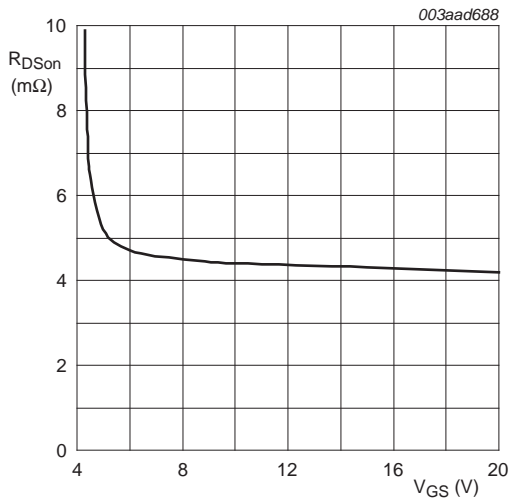
$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

Fig 9. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



$$T_j = 25 \text{ }^\circ\text{C}; I_D = 25 \text{ A}$$

Fig 11. Drain-source on-state resistance as a function of gate-source voltage; typical values

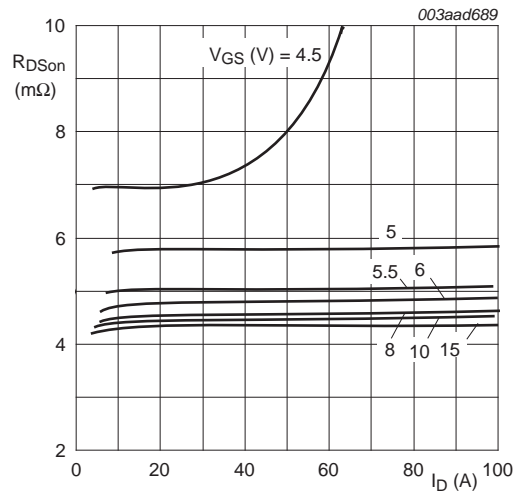
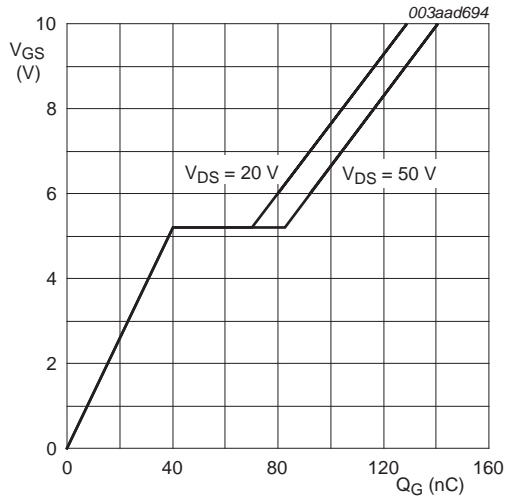
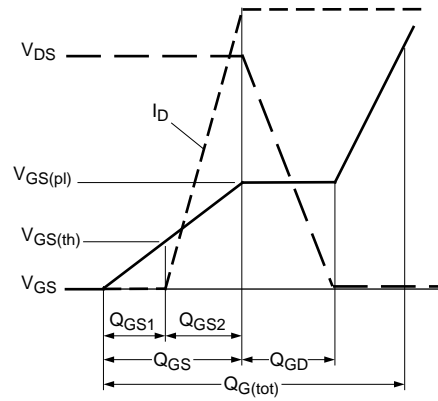


Fig 12. Drain-source on-state resistance as a function of drain current; typical values



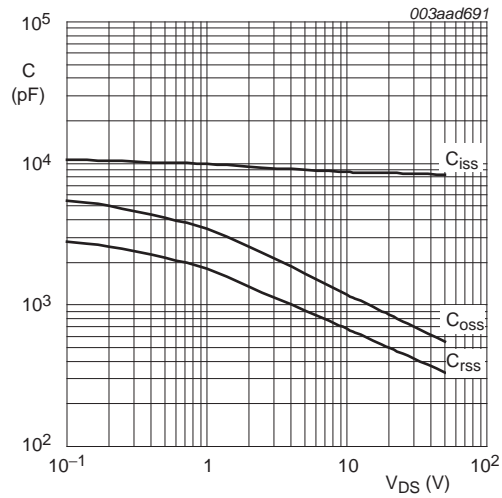
$T_j = 25\text{ }^\circ\text{C}; I_D = 80\text{ A}$

Fig 13. Gate-source voltage as a function of gate charge; typical values



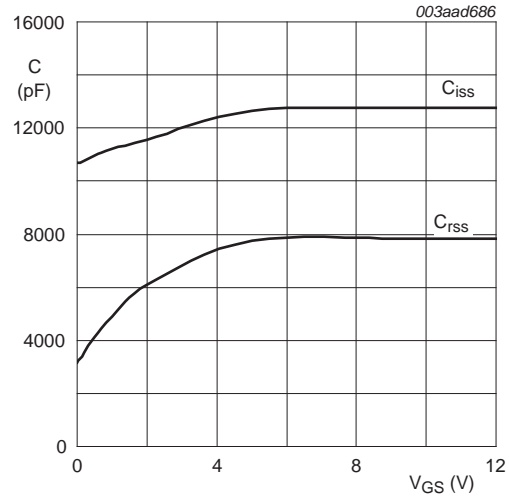
003aaa508

Fig 14. Gate charge waveform definitions



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$f = 1\text{ MHz}; V_{DS} = 0\text{ V};$

Fig 16. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

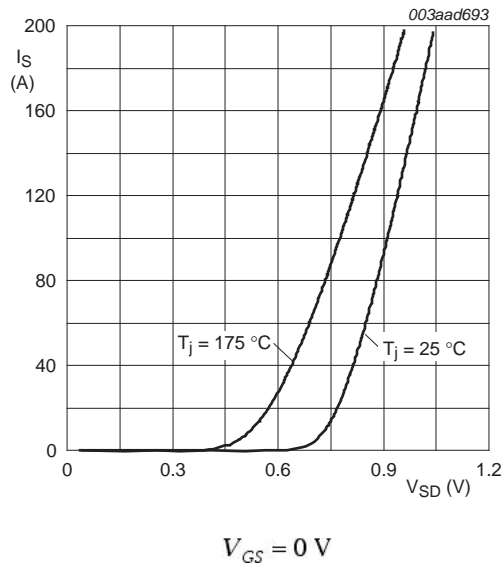


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

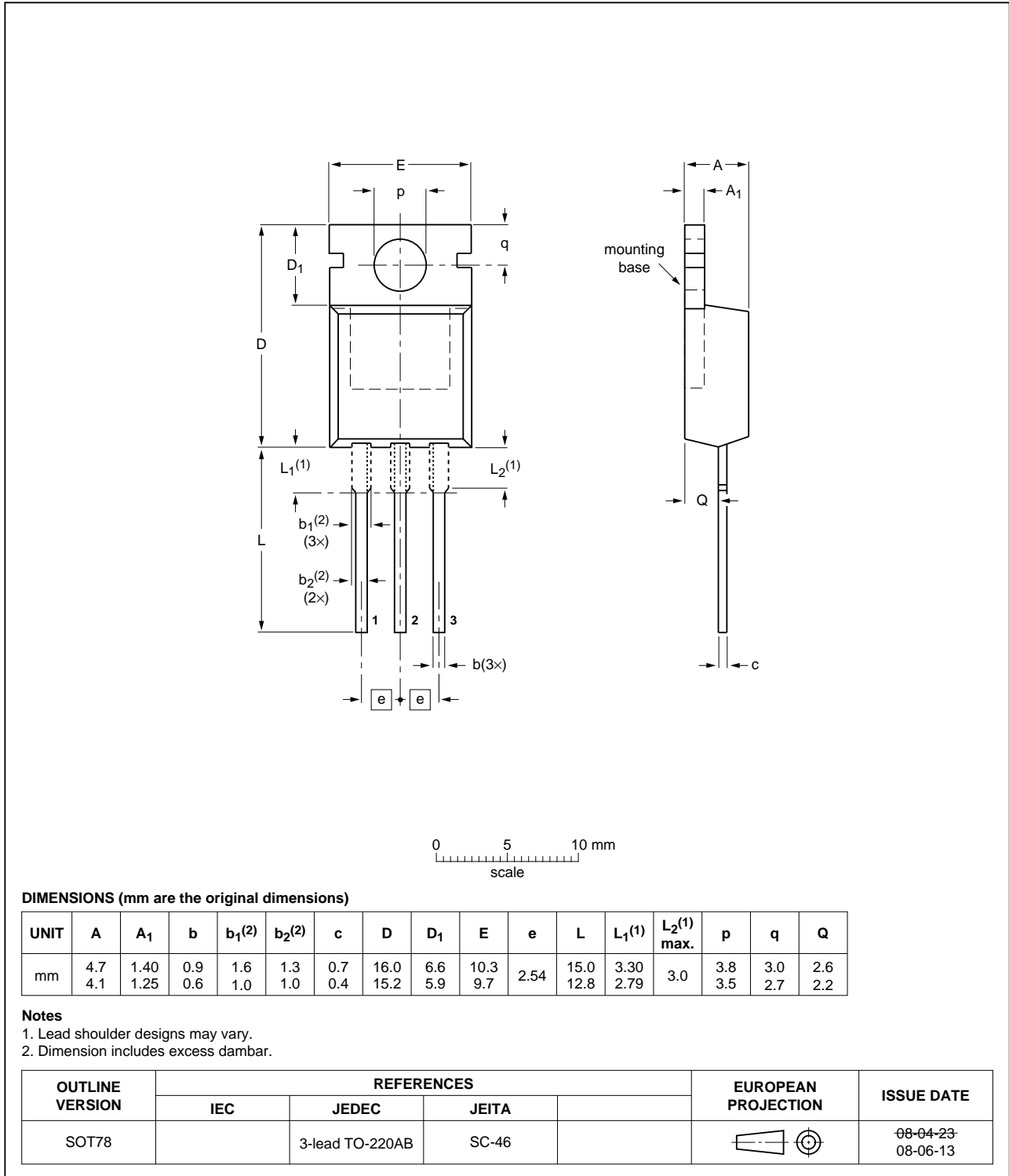


Fig 18. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN5R6-100PS v.4	20120208	Product data sheet	-	PSMN5R6-100PS v.3
Modifications:	• Various changes to content.			
PSMN5R6-100PS v.3	20101202	Product data sheet	-	PSMN5R6-100PS v.2

9. Legal information

9.1 Data sheet status

Document status ^[1] ^[2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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